

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Manoj K. Jain                      Art Unit: 2814  
Serial No.: 10/006,578                      Examiner: Le, T.  
Filing Date: 12/06/01                      Docket No.: TI-31858  
Title: PREVENTION OF CONTACT FAILURE BY HYDROGEN  
TREATMENT

#  
8/13  
11-8-02  
J. Actis

Amendment under 37 CFR 1.115

Assistant Commissioner of Patents  
Washington, DC 20231

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OCT 31 2002

TECHNOLOGY CENTER 2800

Dear Sir:

The following amendments and remarks are offered in response to the Examiner's Office Action dated 06/05/02. They are respectfully submitted as a full and complete response to that Action.

Please amend the above-referenced application as follows:

In the Claims:

Amend claim 1 to read as follows:

1. (amended) A method of forming a conductive structure in an integrated circuit, comprising the steps of:
- forming a dielectric layer over a semiconductor body;
  - forming a hole in said dielectric layer;
  - forming a conductive liner in said hole;
  - annealing said conductive liner;
  - treating said conductive liner with hydrogen;
  - forming a conductive barrier over said conductive liner; and